Appl. No. 10/566,802 Amendment and/or Response Reply to Office action of 18 June 2007

## **IN THE ABSTRACT**

Please delete the current Abstract in its entirety and substitute therefore the following New Abstract:

## **NEW ABSTRACT**

Resonant gate driver circuits provide for an efficient switching of, for example, a metal oxide semiconductor field effect transistor. However, often an operation of the resonant gate driver circuit does not allow for an application where high switching frequencies are required. A pre-charging of the inductor of the resonant gate drive circuit is performed. This allows for a highly energy efficient and fast operation of the metal oxide semiconductor field effect transistor.